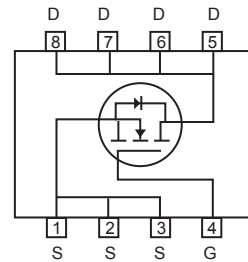
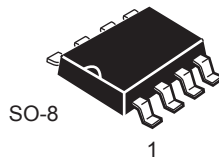


N-Channel Enhancement Mode Field Effect Transistor

PRELIMINARY

FEATURES

- 150V, 4A, $R_{DS(ON)} = 85m\Omega$ @ $V_{GS} = 10V$. □
 $R_{DS(ON)} = 95m\Omega$ @ $V_{GS} = 6V$. □
- Super high dense cell design for extremely low $R_{DS(ON)}$.
- High power and current handling capability.
- Lead-free plating ; RoHS compliant.
- Surface mount Package.



ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ C$ unless otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage(Typ)	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 30	V
Drain Current-Continuous	I_D	4	A
Drain Current-Pulsed ^a	I_{DM}	16	A
Maximum Power Dissipation	P_D	2.5	W
Operating and Store Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Limit	Units
Thermal Resistance, Junction-to-Ambient ^b	$R_{\theta JA}$	50	$^\circ C/W$



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Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$		150		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 135V, V_{GS} = 0V$			1	μA
Gate Body Leakage Current, Forward	I_{GSSF}	$V_{GS} = 30V, V_{DS} = 0V$			100	nA
Gate Body Leakage Current, Reverse	I_{GSSR}	$V_{GS} = -30V, V_{DS} = 0V$			-100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	2		4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 3.3A$		62	85	$m\Omega$
		$V_{GS} = 6V, I_D = 3.0A$		70	95	$m\Omega$
Gate input resistance	R_g	$f=1\text{MHz}, \text{open Drain}$		1		Ω
Dynamic Characteristics ^c						
Input Capacitance	C_{iss}	$V_{DS} = 30V, V_{GS} = 0V, f = 1.0 \text{ MHz}$		1355		pF
Output Capacitance	C_{oss}			130		pF
Reverse Transfer Capacitance	C_{rss}			50		pF
Switching Characteristics ^c						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 75V, I_D = 3.5A, V_{GS} = 10V, R_{GEN} = 6\Omega$		18		ns
Turn-On Rise Time	t_r			5	10	ns
Turn-Off Delay Time	$t_{d(off)}$			35		ns
Turn-Off Fall Time	t_f			5	10	ns
Total Gate Charge	Q_g	$V_{DS} = 75V, I_D = 3.5A, V_{GS} = 10V$		23		nC
Gate-Source Charge	Q_{gs}			5		nC
Gate-Drain Charge	Q_{gd}			6		nC
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Current	I_S				2	A
Drain-Source Diode Forward Voltage ^b	V_{SD}	$V_{GS} = 0V, I_S = 2A$			1.2	V

Notes : □

a.Repetitive Rating : Pulse width limited by maximum junction temperature.

b.Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$. □

c.Guaranteed by design, not subject to production testing. □



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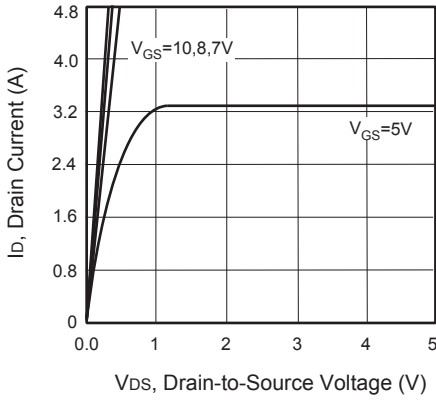


Figure 1. Output Characteristics

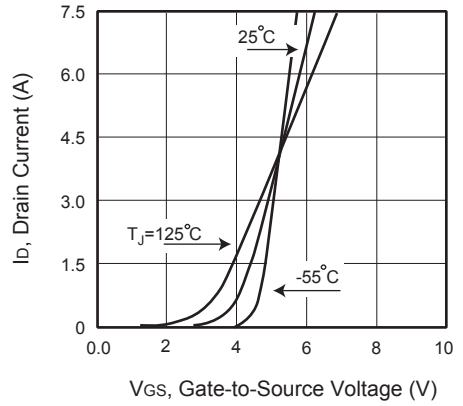


Figure 2. Transfer Characteristics

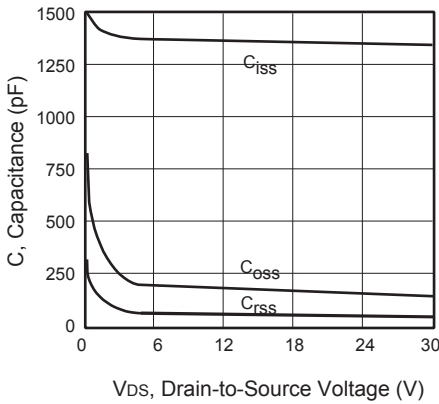


Figure 3. Capacitance

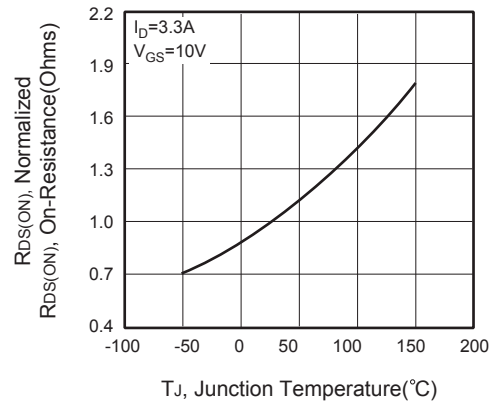


Figure 4. On-Resistance Variation with Temperature

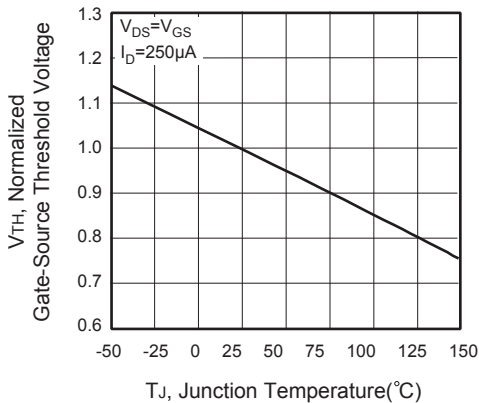


Figure 5. Gate Threshold Variation with Temperature

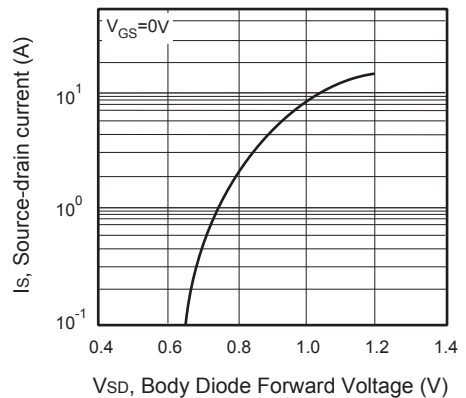


Figure 6. Body Diode Forward Voltage Variation with Source Current



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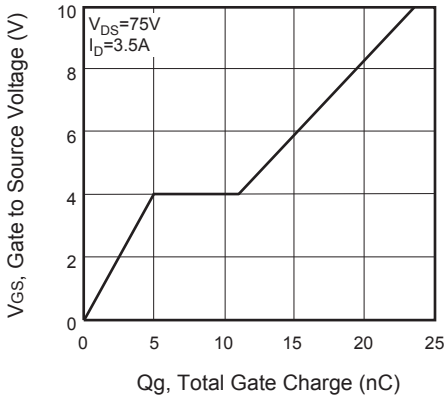


Figure 7. Gate Charge

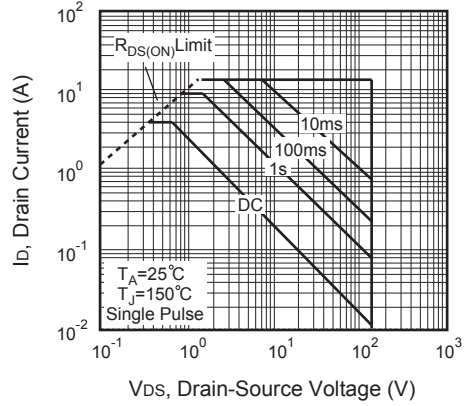


Figure 8. Maximum Safe Operating Area

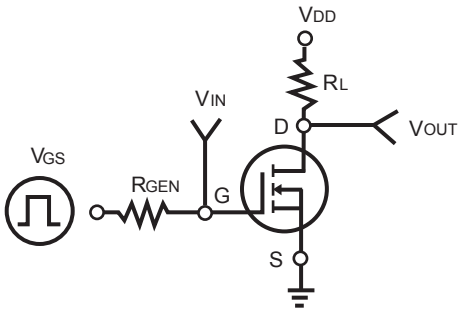


Figure 9. Switching Test Circuit

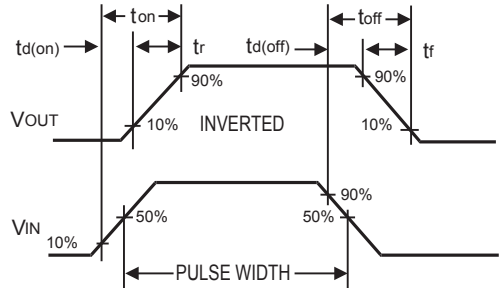


Figure 10. Switching Waveforms

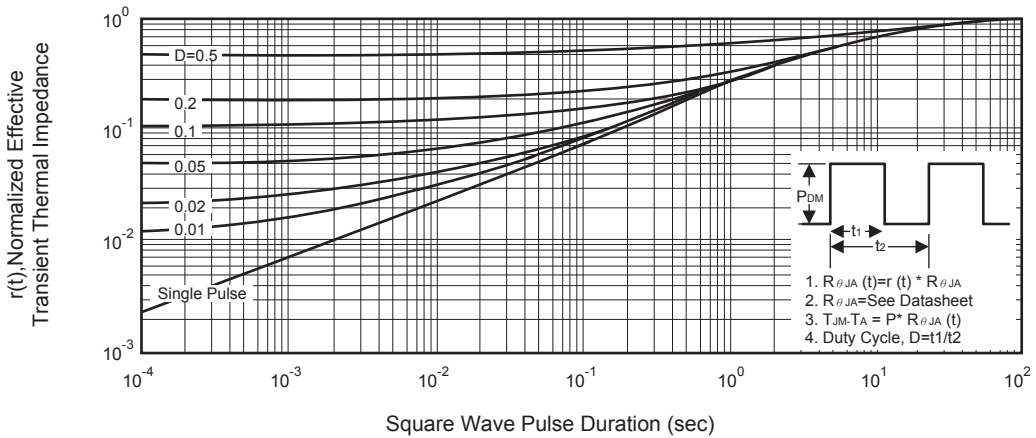


Figure 11. Normalized Thermal Transient Impedance Curve